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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No.: 16907-1577

In re patent application of

Hitoshi TSUNO

Serial No.: 10/676,264

Group Art Unit: 2826

Filed: October 2, 2003

Examiner: Fetsum Abraham

For: SEMICONDUCTOR DEVICE INCLUDING MOS FIELD EFFECT TRANSISTOR
HAVING OFFSET SPACERS OR GATE SIDEWALL FILMS ON EITHER SIDE OF
GATE ELECTRODE AND METHOD OF MANUFACTURING THE SAME

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated August 9, 2004, Applicant hereby elects the claims of Group I, claims 1-14, for prosecution in the subject application.

Upon allowance of the elected claims, Applicant will be permitted to request rejoinder in accordance with MPEP 821.04 and *In re Ochiai*, 71 F.3d 1565 USPQ2d 1127 (Fed. Cir. 1995) of method claims 15-22.

Receipt of the initial Office Action on the merits is awaited.

Respectfully submitted,

Date September 7, 2004

By 

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